IN THE CLAIMS

1. (currently amended) A method of producing an acoustic resonator device, comprising:

depositing a first metal film directly on a substrate;

patterning said first metal film to form an electrode region;

depositing piezoelectric material on said ~~first metal film~~electrode region to form a single, continuous piezoelectric layer;

depositing a second metal film on said single piezoelectric layer;

patterning said second metal film to form a plurality of spaced apart electrodes; and

removing the ~~some or all~~ piezoelectric material from a region of the piezolelectric layer underneath the spaced apart region between said electrodes ~~said single piezoelectric layer not involved in signal transmission~~ by a selective etching process to limit lateral propagation losses to un-etched regions of the acoustic resonator device, said removing step being performed after said second metal film is patterned.

2-9. (canceled)

10. (original) The method of claim 1, wherein said piezoelectric material is selected from the group comprising at least AIN, ZnO and CdS.

11. (previously presented) The method of claim 1, wherein said first and second metal films are formed by lithographic patterning of A1 metal or other conductors.

12. (previously presented) The method of claim 1, wherein said substrate is formed as a plurality of acoustic reflecting layers on a substrate formed from one of a silicon,

quartz or glass wafer.

13. (currently amended) A method of isolating an acoustic resonator device, comprising:

depositing a first metal film directly on a substrate;

depositing piezoelectric material on said first metal film to form a single, continuous piezoelectric layer;

depositing a second metal film on said single piezoelectric layer;

patterning the second metal film to form a plurality of spaced apart electrodes; and

removing ~~some or all~~the piezoelectric material from said single piezoelectric layer ~~not~~ underlying the spaced apart region between the electrodes ~~involved in signal transmission~~ with a selective etching process to limit propagation of energy in lateral modes, said removing step being performed after said second metal film is deposited on said single piezoelectric layer and patterned.

14. (canceled)

15. (previously presented) The method of claim 13, wherein at least some of the substrate surface is removed by selective etching.

16. (original) The method of claim 13, wherein at least some of the removed piezoelectric material forms a void which is back filled with a different material.

17-32. (canceled)